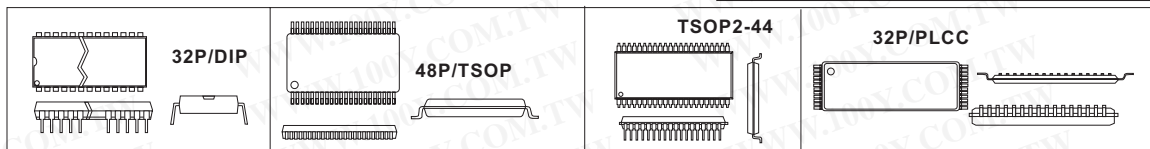


记忆IC

快闪式记忆体

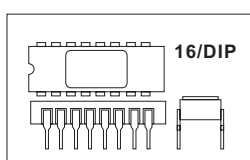
详细产品规格 - 请点击 cn.100y.com.tw



100Y 编号	厂商编号	制造厂商	说明	Pin/Package	Size	Organisation	Access Time	Supply Volt.
18644	TC58DVM92A2TG00	TOSHIBA	4M CMOS flash memory(Pb Free)	TSOP	4Mb	512K*8		
23610	TC58V64BFT	TOSHIBA	CMOS NAND EEPROM	44P/TSOP	8M *8 BIT	64M		2.7 V ~3.6 V
18992	TE28F016B3TA110	INTEL	FLASH	TSOP	16M			
18990	TE28F016B3TA90	INTEL	FLASH	TSOP	16M			3V
18991	TE28F128J3C150	INTEL	FLASH	TSOP	128M		150ns	
23613	TE28F160B3TA110	INTEL	3-Volt Advanced Boot Block Flash Memory	48P/TSOP	16M		110ns	3V
23614	TE28F160C3BA110	INTEL	Boot Block Flash Memory	48P/TSOP	16M		110ns	3V
18994	TE28F160C3BD-70	INTEL	FLASH	TSOP			70ns	
23615	TE28F160C3TC-70	INTEL	Boot Block Flash Memory	48P/TSOP	16M		70ns	3V
18995	TE28F160C3TD-70	INTEL	FLASH	TSOP			70ns	
12817	TE28F160S375	INTEL	Word-wide FlashFile memory	56P/TSOP	16M	2M*8/1M*16	75ns	5V
18996	TE28F320C3BA100	INTEL	FLASH	TSOP	32M		100ns	
18997	TE28F320C3BC-70	INTEL	FLASH	48P/TSOP			70ns	
23617	TE28F320C3BD70	INTEL	Boot Block Flash Memory	48P/TSOP	32M		70ns	3.0V
23620	TE28F320C3TD-70	INTEL	Boot Block Flash Memory	48P/TSOP	32M		70ns	3.0V
18998	TE28F400B3T110	INTEL	FLASH	TSOP	4M			
18999	TE28F640J3C-115	INTEL	FLASH	TSOP			115ns	
18974	TE28F800B3BA90	INTEL	FLASH	TSOP				
18975	TE28F800B5B-90	INTEL	FLASH	48P/TSOP				
18976	TE28F800C3B90	INTEL	Flash Memory	TSOP	4Mbit	256kbit*16	90ns	2.7~3.6V
19000	TMS28F010A-15C4FML	T.I.	1048576-BIT FLASH ELECTRICALLY ERASABLE PROGRAMMABLE READ-ONLY MEMORY	32P/PLCC	1M	128K*8	150ns	5.5V
19001	TMS28F010B-10C4FMQ	T.I.	131072 BY 8-BIT FLASH MEMORY	32P/PLCC	1M	131072 * 8	100ns	5.5V
19002	TMS28F010B-12C4FME	T.I.	131072 BY 8-BIT FLASH MEMORY	32P/PLCC	1M	131072 * 8	120ns	5.5V
19003	TMS28F010B-12C4FML	T.I.	131072 BY 8-BIT FLASH MEMORY	32P/PLCC	1M	131072 * 8	100ns	5.5V
19004	TMS28F010B-12C4FMQ	T.I.	131072 BY 8-BIT FLASH MEMORY	32P/PLCC	1M	131072 * 8	100ns	5.5V
19005	TMS28F010B-12C5FME	T.I.	131072 BY 8-BIT FLASH MEMORY	32P/PLCC	1M	131072 * 8	120ns	5.5V
19006	TMS28F010B-12C5FML	T.I.	131072 BY 8-BIT FLASH MEMORY	32P/PLCC	1M	131072 * 8	120ns	5.5V
19007	TMS28F010B-15C4FML	T.I.	131072 BY 8-BIT FLASH MEMORY	32P/PLCC	1M	131072 * 8	150ns	5.5V
19008	TMS28F010B-90C5FML	T.I.	131072 BY 8-BIT FLASH MEMORY	32P/PLCC	1M	131072*8	90ns	5.5V
23516	TMS28F512A-12C4FMQ	T.I.	FLASH MEMORY	32P/PLCC		65536 by 8 Bits	120 ns	5.5 V
19010	TMS28F512A-15C4FME	T.I.	FLASH MEMORY	32P/PLCC	512K	64K*8	150ns	5.5V
19011	TMS28F512A-15C4FML	T.I.	FLASH MEMORY	32P/PLCC	512K	64K*8	150ns	5.5V
11833	TMS28F512A-15FME	T.I.	FLASH MEMORY	32P/PLCC	512K	64K*8	100ns	5.5V
19009	TMS28F512A-15FMQ	T.I.	FLASH MEMORY	32P/PLCC	512K	64K*8	120ns	5.5V
19013	TMS29F002RT-12BFML	T.I.	262144 BY 8-BIT FLASH MEMORIES	32P/PLCC	2M	26144*8	120ns	5V
19014	TMS29F040-12C5DDE	T.I.	524288 BY 8-BIT FLASH MEMORY	32P/TSOP	4M	524288*8	120ns	5V
19017	TMS29F040-12C5DDL	T.I.	524288 BY 8-BIT FLASH MEMORY	32P/TSOP	4M	524288*8	120ns	5V
19018	TMS29F040-12C5FME	T.I.	524288 BY 8-BIT FLASH MEMORY	32P/PLCC	4M	524288*8	120ns	5V
19019	TMS29F040-90C5DDE	T.I.	524288 BY 8-BIT FLASH MEMORY	32P/TSOP	4M	524288*8	90ns	5V
19020	TMS29F040-90C5DDL	T.I.	524288 BY 8-BIT FLASH MEMORY	32P/TSOP	4M	524288*8	90ns	5V
19021	TMS29F040-90C5FML	T.I.	524288 BY 8-BIT FLASH MEMORY	32P/PLCC	4M	524288*8	90ns	5V
10946	W29C011A-15	WINBOND	128K x 8 CMOS flash memory	32P/DIP	1Mb	128K x 8	150ns	5V
14148	W29C020C-90B	WINBOND	256K x 8 CMOS FLASH MEMORY	32P/DIP	2M	256K*8	90ns	5V
46408	W29C020C-90Z	WINBOND	快闪式记忆体	DIP-32	2M	256K*8	90ns	
11825	W29C020CP-90B	WINBOND	256K*8 CMOS flash memory	32P/PLCC	2M	256K*8	90ns	5V
46409	W29C020CP90Z	WINBOND	256K*8 CMOS STATIC RAM	PLCC-32	2M	256*8	90	
19023	W29C020CT-90B	WINBOND	128K*8 CMOS flash memory	32P/TSOP	2M	128K*8	90ns	5V
10947	W29C040-90B	WINBOND	512K*8 CMOS flash memory	32P/DIP	4Mb	512K*8	90ns	5V
46459	W29C040-90Z	WINBOND	快闪式记忆体	DIP-32P	4M	512K*8	90ns	12
17704	W29C040P-70B	WINBOND	512K*8 CMOS flash memory	32P/PLCC	4Mb	512K*8	70ns	5V
22881	W29C040P-90B	WINBOND	512K*8 CMOS flash memory	32P/PLCC	4Mb	512K*8	90ns	5V
19024	W29EE011P-90	WINBOND	128K*8 CMOS flash memory	32P/PLCC	1M	128K*8	90ns	5V
33546	W39L040P-70B	WINBOND	512K*8 CMOS FLASH MEMORY	32P/PLCC	4Mbit	512K*8	70ns	3.3V

动态式记忆体 D-RAM

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100Y 编号	厂商编号	制造厂商	说明	Organisation	Package
48597	KM4164B-12	SAMSUNG	64K x 1-bit Dynamic Nmos Ram	64k x 1-bit	16P/DIP
48547	LH21256-10	SHARP	DRAM		16P/DIP
48503	LH21256-12	SHARP	DRAM		16P/DIP
48605	M5K4164ANP-15	MITSUBISHI	64K x 1-bit Dynamic Nmos Ram	64k x 1-bit	16P/DIP
48516	MB81256-10	FUJITSU	DRAM		16P/DIP



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